

2PC4081 NPN general-purpose transistor Rev. 06 — 17 November 2009

Product data sheet

Product profile 1.

1.1 General description

NPN transistor in a SOT323 (SC-70) plastic package. The PNP complement is 2PA1576.

1.2 Features

- Low current (max. 150 mA)
- Low voltage (max. 50 V)

1.3 Applications

- General-purpose switching
- Small signal amplification

2. **Pinning information**

Table 1. **Pinning**

Pin	Description	Simplified outline	Symbol
1	base	<u> </u>	
2	emitter	3	3
3	collector	1 2	1 —
			sym021

Ordering information 3.

Table 2. **Ordering information**

Type number	Package					
	Name	Description	Version			
2PC4081Q	SC-70	plastic surface mounted package; 3 leads	SOT323			
2PC4081R						
2PC4081S	_					



NXP Semiconductors 2PC4081

NPN general-purpose transistor

4. Marking

Table 3. Marking codes

Type number	Marking code ^[1]
2PC4081Q	Z*Q
2PC4081R	Z*R
2PC4081S	Z*S

^{[1] * = -:} made in Hong Kong

5. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	60	V
V_{CEO}	collector-emitter voltage	open base	-	50	V
V_{EBO}	emitter-base voltage	open collector	-	7	V
I _C	collector current (DC)		-	150	mA
I _{CM}	peak collector current		-	200	mA
I _{BM}	peak base current		-	200	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	<u>[1]</u> _	200	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C

^[1] Transistor mounted on an FR4 printed-circuit board, single-sided copper, tin-plated and standard footprint.

6. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient		<u>[1]</u> -	-	625	K/W

^[1] Transistor mounted on an FR4 printed-circuit board, single-sided copper, tin-plated and standard footprint.

^{* =} t: made in Malaysia

NXP Semiconductors 2PC4081

NPN general-purpose transistor

7. Characteristics

Table 6. Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

Parameter	Conditions	Min	Tvp	Max	Unit
		•••••	.,,,,		
collector-base cut-off current	$I_E = 0 \text{ A}; V_{CB} = 30 \text{ V}$	-	-	100	nA
	$I_E = 0 \text{ A}; V_{CB} = 30 \text{ V};$ $T_j = 150 \text{ °C}$	-	-	5	μА
emitter-base cut-off current	$I_C = 0 A; V_{EB} = 4 V$	-	-	100	nA
DC current gain	$I_C = 1 \text{ mA}; V_{CE} = 6 \text{ V}$				
2PC4081Q		120	-	270	
2PC4081R		180	-	390	
2PC4081S		270	-	560	
collector-emitter saturation voltage	$I_C = 50 \text{ mA}; I_B = 5 \text{ mA}$	[1] -	-	400	mV
collector capacitance	$I_E = i_e = 0 \text{ A};$ $V_{CB} = 12 \text{ V}; f = 1 \text{ MHz}$	-	2	3.5	pF
transition frequency	$I_C = 2 \text{ mA}; V_{CE} = 12 \text{ V};$ f = 100 MHz	100	-	-	MHz
	emitter-base cut-off current DC current gain 2PC4081Q 2PC4081R 2PC4081S collector-emitter saturation voltage collector capacitance transition	$ \begin{array}{lll} \text{collector-base} & I_E = 0 \text{ A; } V_{CB} = 30 \text{ V} \\ I_E = 0 \text{ A; } V_{CB} = 30 \text{ V;} \\ T_j = 150 \text{ °C} \\ \\ \text{emitter-base} & I_C = 0 \text{ A; } V_{EB} = 4 \text{ V} \\ \\ \text{DC current gain} & I_C = 1 \text{ mA; } V_{CE} = 6 \text{ V} \\ \\ \text{2PC4081Q} & \\ \text{2PC4081S} \\ \\ \text{collector-emitter saturation} & I_C = 50 \text{ mA; } I_B = 5 \text{ mA} \\ \\ \text{collector} & I_E = i_e = 0 \text{ A;} \\ \\ \text{voltage} & \\ \\ \text{collector capacitance} & V_{CB} = 12 \text{ V; } f = 1 \text{ MHz} \\ \\ \text{transition} & I_C = 2 \text{ mA; } V_{CE} = 12 \text{ V;} \\ \end{array} $	$ \begin{array}{llllllllllllllllllllllllllllllllllll$	$ \begin{array}{llllllllllllllllllllllllllllllllllll$	$ \begin{array}{c} \text{collector-base} \\ \text{cut-off current} \\ \hline \\ I_E = 0 \text{ A; V}_{CB} = 30 \text{ V;} \\ \hline \\ I_E = 0 \text{ A; V}_{CB} = 30 \text{ V;} \\ \hline \\ T_j = 150 \text{ °C} \\ \hline \\ \text{emitter-base} \\ \text{cut-off current} \\ \hline \\ DC \text{ current gain} \\ \hline \\ DC \text{ current gain} \\ \hline \\ DC \text{ current gain} \\ \hline \\ 2PC4081Q \\ \hline \\ 2PC4081R \\ \hline \\ 2PC4081S \\ \hline \\ 2PC4081S \\ \hline \\ collector-emitter \\ \text{saturation} \\ \text{voltage} \\ \hline \\ \text{collector} \\ \hline \\ collector \\ \text{capacitance} \\ \hline \\ I_C = 50 \text{ mA; I}_B = 5 \text{ mA} \\ \hline \\ I_C = 50 \text{ mA; I}_B = 5 \text{ mA} \\ \hline \\ I_C = 1 \text{ mA; V}_{CE} = 1 \text{ MHz} \\ \hline \\ \hline \\ \text{transition} \\ \hline \\ I_C = 2 \text{ mA; V}_{CE} = 12 \text{ V; } \\ \hline \\ 100 \\ \hline \\$

^[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

NXP Semiconductors

Package outline 8.

Plastic surface-mounted package; 3 leads **SOT323** В Α X H_{E} = v (M) A Q **→** | w (M) B е detail X 2 mm scale **DIMENSIONS** (mm are the original dimensions) UNIT D С Ε Q bp e₁ ΗE $L_{\mathbf{p}}$ w max 0.25 1.35 0.23 0.1 1.3 0.65 0.2 0.2 mm 0.8 0.10 1.15 0.15 REFERENCES **EUROPEAN** OUTLINE **ISSUE DATE** PROJECTION VERSION IEC **JEDEC JEITA** 04-11-04 SOT323 SC-70

Package outline SOT323 (SC-70) Fig 1.

© NXP B.V. 2009. All rights reserved.

06-03-16

NXP Semiconductors

NPN general-purpose transistor

5 of 7

Revision history

Table 7. **Revision history**

Product data sheet

Document ID	Release date	Data sheet status	Change notice	Supersedes
2PC4081_6	20091117	Product data sheet	-	2PC4081_5
Modifications:	including ned content.	eet was changed to reflect t w legal definitions and discla	aimers. No changes w	
	• Figure 1 "Pa	ckage outline SOT323 (SC-	<u>70)"</u> : updated	
2PC4081_5	20041125	Product data sheet	-	2PC4081_4
2PC4081 4	19990408	Product specification	-	2PC4081_3
21 0 1001_1				
2PC4081_3	19970704	Product specification	-	2PC4081_2

NXP Semiconductors 2PC4081

NPN general-purpose transistor

10. Legal information

10.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

10.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

10.3 Disclaimers

General — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental

damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) may cause permanent damage to the device. Limiting values are stress ratings only and operation of the device at these or any other conditions above those given in the Characteristics sections of this document is not implied. Exposure to limiting values for extended periods may affect device reliability.

Terms and conditions of sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nxp.com/profile/terms, including those pertaining to warranty, intellectual property rights infringement and limitation of liability, unless explicitly otherwise agreed to in writing by NXP Semiconductors. In case of any inconsistency or conflict between information in this document and such terms and conditions, the latter will prevail.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from national authorities.

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

10.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

11. Contact information

For more information, please visit: http://www.nxp.com

For sales office addresses, please send an email to: salesaddresses@nxp.com

2PC4081_6 © NXP B.V. 2009. All rights reserved

2PC4081 **NXP Semiconductors**

NPN general-purpose transistor

12. Contents

1	Product profile	1
1.1	General description	1
1.2	Features	
1.3	Applications	1
2	Pinning information	1
3	Ordering information	1
4	Marking	2
5	Limiting values	2
6	Thermal characteristics	2
7	Characteristics	3
8	Package outline	4
9	Revision history	5
10	Legal information	6
10.1	Data sheet status	6
10.2	Definitions	6
10.3	Disclaimers	6
10.4	Trademarks	6
11	Contact information	6
12	Contents	7

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.



All rights reserved.



founded by